Circuit Ideas

Simple tester for f.e.ts

Zero-bias drain current, gate cut-off voltage and gate leakage current in junction f.e.ts can be measured with a high-impedance voltmeter $(20,000 \Omega/V)$ or better) using the circuits shown in figures (a), (b) and (c) respectively. Using an external voltmeter, a simple tester can be built around three push-button switches as shown (right). With the source resistor value of $1k\Omega$, IDDS is read in mA on the voltage scales of the meter. Two small 9-V batteries give sufficient voltage to test most f.e.ts. The f.e.t. is protected by the protec-

loadline principle, and limits the power to the test circuit to about 200mW.

The circuit has an additional refinement.

By depressing the V_P button and the I_{DSS} button simultaneously, the circuit shown in (d) is made. The meter reading now gives both drain current in mA and gate-source voltage in volts, thus giving a third point on the I_DV_{GS} characteristic.

The complete tester can be built in a box measuring $10 \times 7 \times 5$ cm.

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